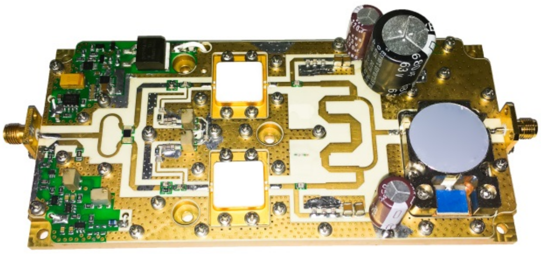
RAP2729P60; 2.7 GHz – 2.9 GHz 1000 W AMPLIFIER

- **Solid-state Class AB design**
- **GaN on SiC Transistors**
- **High reliability and ruggedness**
- **Small Dimensions & Light Weight**
- **Fast Switching Capability**



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

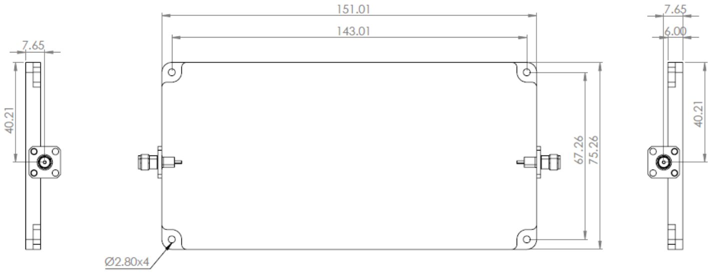
Frequency:	2.7-2.9 GHz
Output Power:	1000 W Typ. %10 300µs
Nominal Gain:	10 dB
Gain Flatness:	± 1 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1
DC Supply Voltage:	50 V
Efficiency:	% 55 Min.
Enable Speed:	1 µs max.
Pulse Droop :	0.5 dB
Rise / Fall Time	50 nsec max.
Operating Case Temp.:	-40 ºC to 85 ºC
Storage Temperature:	-40 ºC to 85 ºC
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	SMA Female
50 V :	Solder Pad
GND :	Solder Pad
Enable :	Solder Pad

MECHANICAL SPECIFICATIONS

Size (mm) :	151x75.3
Weight :	275 gr.
Plating :	Yellow Chromate



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